ShiLing®

ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

Specifcation of products

:

:MDST200A-H4

ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

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Module Type

◆Diode

Maximum Ratings

Symbol	Item	Conditions	Values	Units
I_D	Output Current(D.C.)	Tc=96℃ Three phase full wave	200	A
[illegible]	[illegible]forward current	t=10mS Tvj =45℃	1900	A
[illegible]	[illegible]		18050	A^2s
[illegible]	[illegible]	[illegible]Zr.m.s.;1min	3000	V
[illegible]	[illegible]	[illegible]	-40 to +150	℃
[illegible]	[illegible]	[illegible]	[illegible]	℃

◆Thyristor

Maximum Ratings

Symbol	Item	Conditions	Values	Units
I_{TAV} ℃	Average On-State Current	Tc=93℃, Single Phase half wave 180° conduction	200	A
I_{TSM}	Surge On-State Current	TVJ=45℃ t=10ms (50Hz), sine VR=0	1900	A
i^2t	Circuit Fusing Consideration		18050	A^2s
Visol	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1 min	3000	V
Tvj	Operating Junction Temperature		-40 to +125	℃
Tstg	Storage Temperature		-40 to +125	℃
Mt	Mounting Torque	To terminals(M4)	25%	Nm
Mt		To terminals(M6)	5±5%	
Ms		To heatsink(M6)	5±5%	Nm
di/dt	Critical Rate of Rise of On-State Current	$T_{VJ}=T_{VJM}$, $V_D=1/2V_{DRM}$,I_G =100mA d_{iG}/d_t=0.1A/μs	200	A/μs
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	$T_J=T_{VJM}$,$V_D=2/3V_{DRM}$,linear volta rise	500	V/μs

Electrical and Thermal Characteristics

Symbol	Item		Min.	Typ.	Max.	Units

Performance Curves













